



#4/H  
7/16/02  
L. Cuyler

In re application of

JOZEF D. MITROS

Serial No. 10/020,034 (TI-32931)

Filed December 7, 2001

For: METHODS FOR FABRICATING LOW CHC  
DEGRADATION MOSFET TRANSISTORS

Art Unit 2823

Examiner Long Pham

Commissioner for Patents  
Washington, D. C. 20231

RECEIVED  
JUL 16 2002  
TECHNICAL STAFF

Sir:

**AMENDMENT UNDER 37 C.F.R. 1.111**

In response to the Office action dated May 30, 2002, please amend the above-identified application as follows:

**In the claims:**

Amend claim 1 as follows:

device, comprising the steps of:

providing a semiconductor device substrate;

implanting a first transistor region associated with a first transistor device in the semiconductor device substrate [using a first implantation process] to adjust a threshold voltage associated with the first transistor device[;] and concurrently implanting a portion